

Silicon PNP Power Transistors

2SA1067

DESCRIPTION

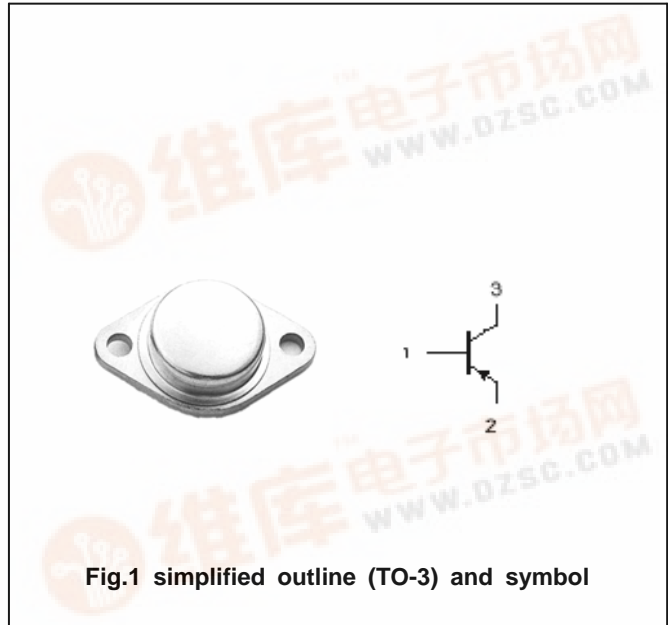
- With TO-3 package
- Low collector saturation voltage
- High transition frequency

APPLICATIONS

- For audio and general purpose amplifier applications

PINNING(see Fig.2)

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector



Absolute maximum ratings(Ta=°C)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V _{CBO}	Collector-base voltage	Open emitter	-120	V
V _{CEO}	Collector-emitter voltage	Open base	-120	V
V _{EBO}	Emitter-base voltage	Open collector	-5	V
I _C	Collector current		-10	A
I _{CM}	Collector current-peak		-14	A
P _C	Collector power dissipation	T _C =25°C	100	W
T _j	Junction temperature		150	°C
T _{stg}	Storage temperature		-65~150	°C

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CHARACTERISTICS

T_j=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-emitter breakdown voltage	I _C =-25mA ; I _B =0	-120			V
V _{CEsat}	Collector-emitter saturation voltage	I _C =-5A ; I _B =-0.5A			-2.0	V
V _{BEsat}	Base-emitter saturation voltage	I _C =-5A ; I _B =-0.5A			-2.5	V
I _{CBO}	Collector cut-off current	V _{CB} =-120V ; I _E =0			-0.1	mA
I _{EBO}	Emitter cut-off current	V _{EB} =-5V ; I _C =0			-0.1	mA
h _{FE}	DC current gain	I _C =-3A ; V _{CE} =-4V	60		150	
f _T	Transition frequency	I _C =-0.5A ; V _{CE} =-10V		50		MHz

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PACKAGE OUTLINE

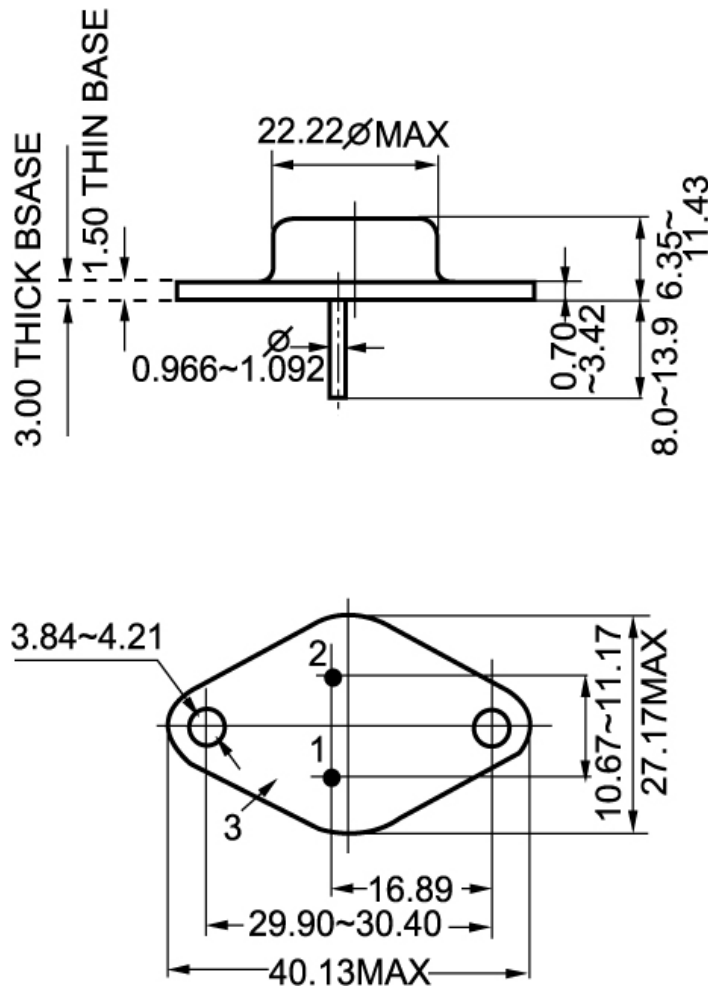


Fig.2 outline dimensions (unindicated tolerance: ± 0.1 mm)